

Description

The 4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38 series combine an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar phototransistor detector in a plastic DIP6 package with different lead forming options.

Features

- High isolation 5000 VRMS
- DC input with transistor output
- Operating temperature range - 55 °C to 110 °C
- RoHS & REACH Compliance
- MSL class 1
- UL-approved: UL1577, File No.E492440

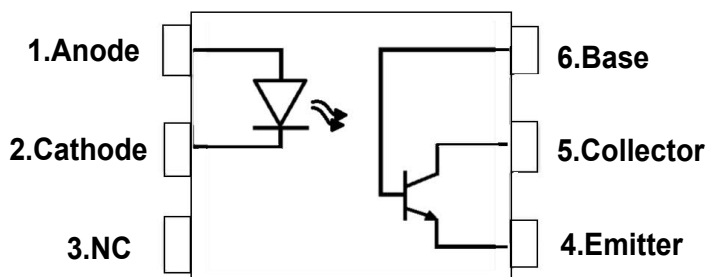
Truth Table (Positive Logic)

Input	Enable	Output
H	H	L
L	H	H
H	L	H
L	L	H
H	NC	L
L	NC	H

Applications

- Sequence controller
- Telephone/FAX
- System appliances, measuring instrument
- Programmable logic controller

Schematics



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT	NOTE
INPUT				
Forward Current	I_F	50	mA	
Peak Forward Current($t=10\mu s$)	I_{FM}	1	A	1
Reverse Voltage	V_R	6	V	
Power Dissipation($T_A=25^\circ C$)	P_D	70	mW	
OUTPUT				
Collector - Emitter Voltage	V_{CEO}	80	V	
Collector-Base Breakdown Voltage	V_{CBO}	80	V	
Emitter - Collector Voltage	V_{ECO}	7	V	
Emitter-Base Breakdown Voltage	V_{EBO}	7	V	
Collector Current	I_C	80	mA	
Power Dissipation($T_A=25^\circ C$)	P_C	150	mW	
COMMON				
Total Power Dissipation	P_{tot}	200	mW	
Isolation Voltage	V_{iso}	5000	V _{rms}	2
Operating Temperature	T_{opr}	-55~+110	$^\circ C$	
Storage Temperature	T_{stg}	-55~+110	$^\circ C$	
Soldering Temperature	T_{sol}	260	$^\circ C$	

Note 1. AC For 1 Minute, R.H. = 40 ~ 60%

Note 2. For 10 seconds

ELECTRICAL OPTICAL CHARACTERISTICS at Ta=25°C

PARAMETER	SYMBOL	MIN	TYP.	MAX	UNIT	TEST CONDITION	NOTE
INPUT							
Forward Voltage	V_F	-	1.24	1.4	V	$I_F=10\text{mA}$	
Reverse Current	I_R	-	-	10	μA	$V_R=6\text{V}$	
Input Capacitance	C_{in}	-	30	-	pF	$V=0, f=1\text{kHz}$	
OUTPUT							
Collector Dark Current	I_{CEO}	-	-	20	nA	$V_{CE}=10\text{V}, I_F=0$	
Collector-Emitter Breakdown Voltage	BV_{CEO}	80	-	-	V	$I_C=1\text{mA}, I_F=0$	
Emitter-Collector Breakdown Voltage	BV_{ECO}	7	-	-	V	$I_E=1\text{mA}, I_F=0$	
Collector-Base Breakdown	BV_{CBO}	80	-	-	V	$I_C=0.1\text{mA}, I_F=0$	
Emitter-Base Breakdown	BV_{EBO}	7	-	-	V	$I_E=0.1\text{mA}, I_F=0$	

TRANSFER CHARACTERISTICS

Current Transfer Ratio	CTR	4N35, 4N36, 4N37	100	-	-	%	IF=10mA, VCE=10V
		4N25,4N26, 4N38	20	-	-		
		4N27, 4N28	10	-	-		
Collector-Emitter Saturation Voltage	V _{CE(sat)}	4N25,4N26, 4N27,4N28	-	-	0.5	V	IF=10mA, VCE=10V
		4N35,4N36,4N37	-	-	0.3		IF= 10mA, IC= 0.5mA
		4N38	-	-	1.0		IF= 20mA, IC= 4mA
		4N25,4N26, 4N27,4N28	-	-	0.5		IF= 50mA, IC= 2mA
Isolation Resistance		R _{IO}	10 ¹²	10 ¹⁴	-	Ω	V _{IO} =500Vdc.
Floating Capacitance		C _{IO}	-	0.2	1	pF	V=0, f=1MHz
Cut-off Frequency		f _c	-	6	-	kHz	VCE=5V, IC=2mA RL=100Ω,-3dB
Turn On Time	t _{on}	4N25,4N26,4N27, 4N28	-	3	15	-	IF= 10mA, VCC= 10V, RL= 100Ω
		4N35,4N36,4N37, 4N38	-	10	12	-	Ic= 2mA, VCC= 10V, RL= 100Ω
Turn Off Time	t _{off}	4N25,4N26,4N27, 4N28	-	3	16	-	IF= 10mA, VCC= 10V, RL= 100Ω
		4N35,4N36,4N37, 4N38	-	9	12	-	Ic= 10mA, VCC= 10V, RL= 100Ω

CHARACTERISTIC CURVES

Fig.1 Forward Current vs. Ambient Temperature

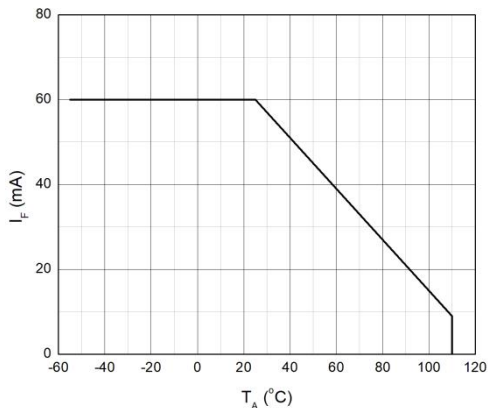


Fig.2 Collector Power Dissipation vs. Ambient Temperature

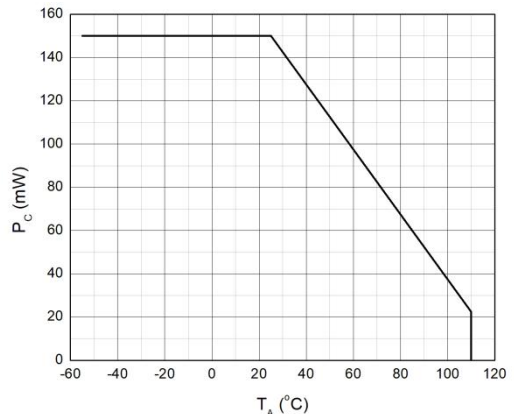


Fig.3 Forward Current vs. Forward Voltage

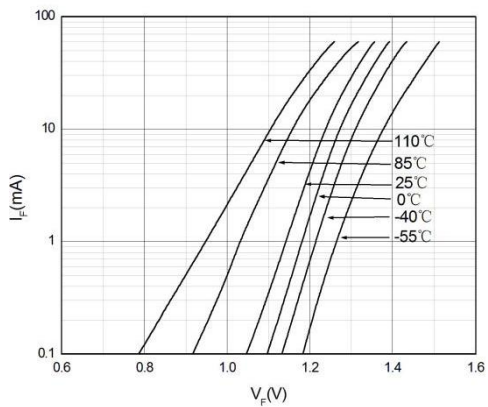


Fig.4 Collector Dark Current vs. Ambient Temperature

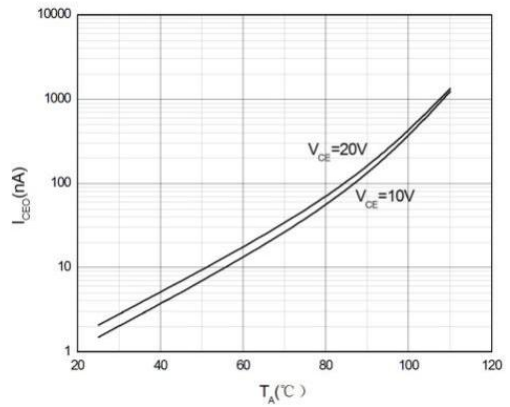


Fig.5 Collector Current vs. Collector-emitter Voltage

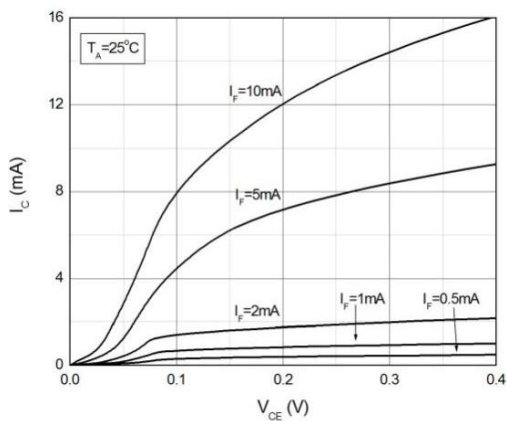
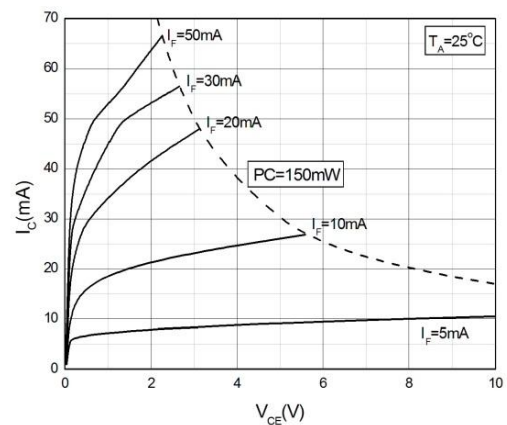


Fig.6 Collector Current vs. Collector-emitter Voltage



CHARACTERISTIC CURVES

Fig.7 Normalized Current Transfer Ratio vs. Forward Current

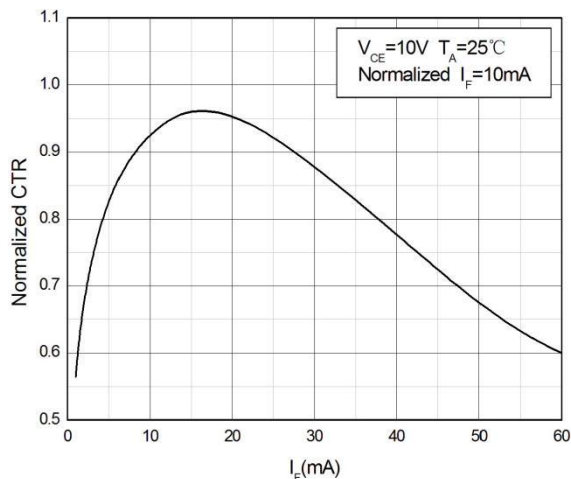


Fig.8 Normalized Current Transfer Ratio vs. Ambient Temperature

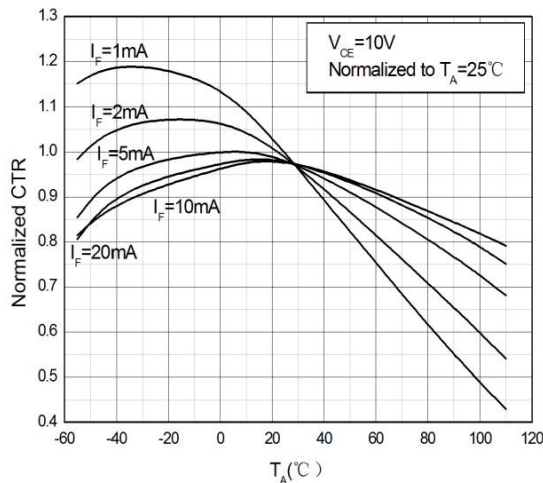


Fig.9 Current Transfer Ratio(Unsaturated) vs Base-Emitter Resistance

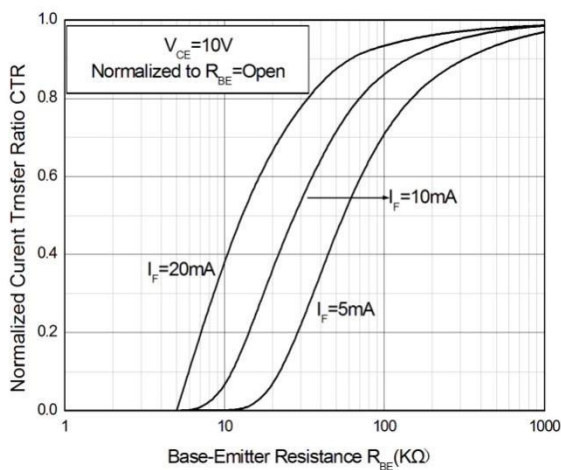
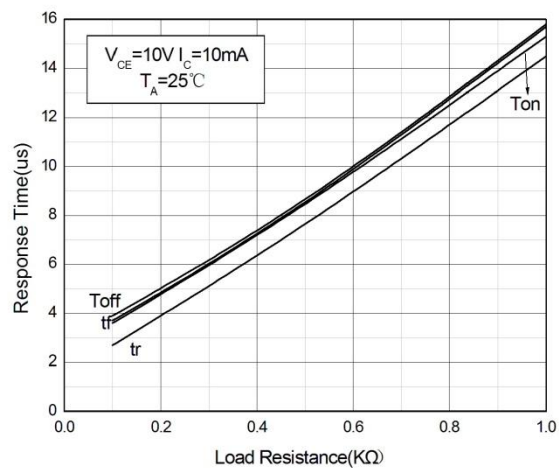
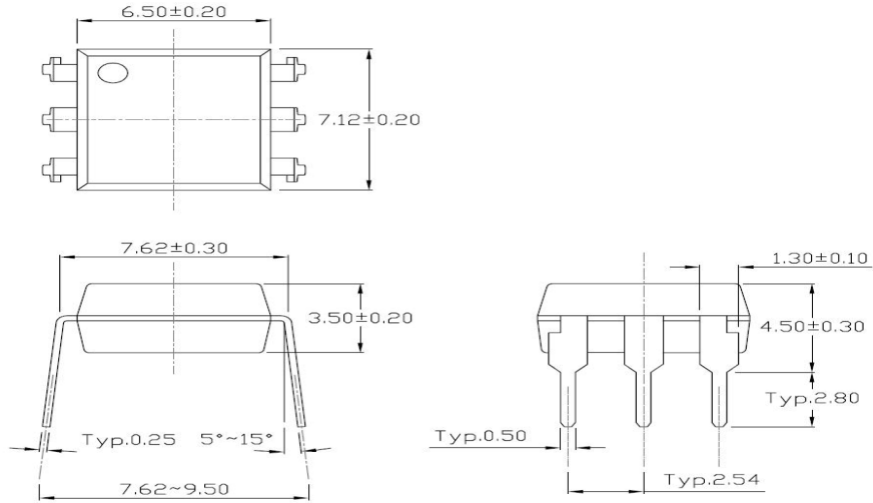


Fig.10 Switching Time vs. Load Resistance



PACKAGE DIMENSIONS (Dimensions in mm unless otherwise stated)

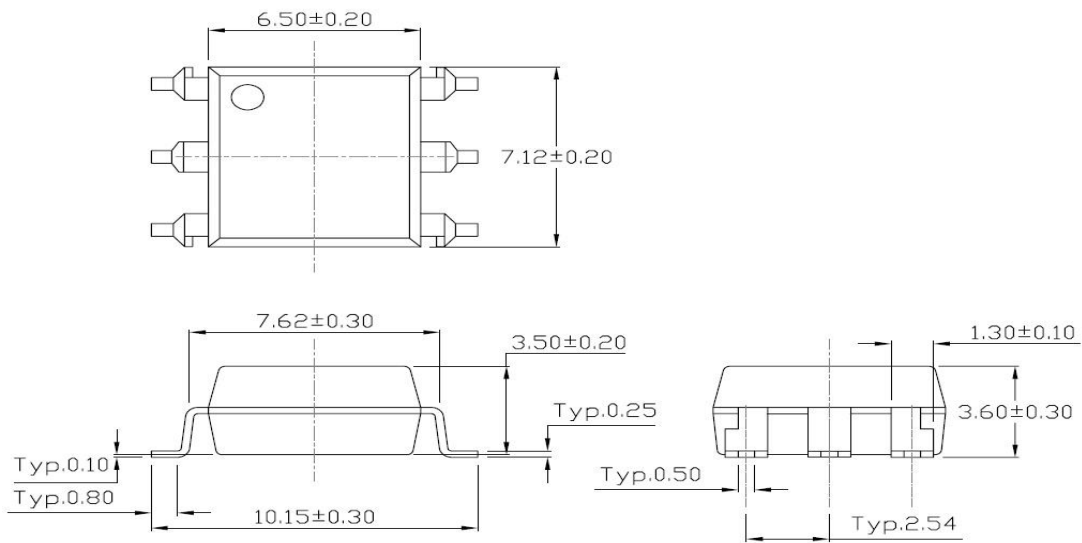
Standard DIP – Through Hole (DIP Type)



Gullwing (400mil) Lead Forming – Through Hole (M Type)

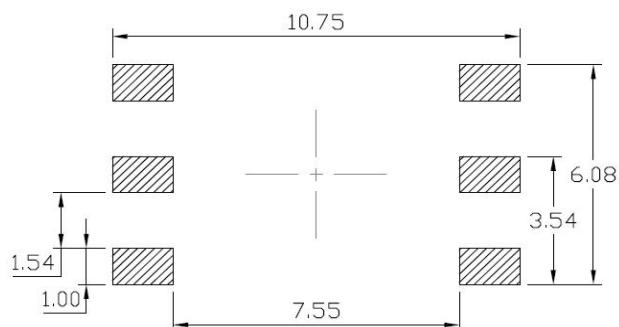
PACKAGE DIMENSIONS (Dimensions in mm unless otherwise stated)

Surface Mount (Low Profile) Lead Forming (SL Type)



Recommended Solder Mask (Dimensions in mm unless otherwise stated)

Surface Mount Lead Forming & Surface Mount (Low Profile) Lead Forming



Marking

UMW
4Nxx
XXWW

- “XX” denotes YEAR;
- “WW” denotes WEEK

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